SKiiP 38NAB066V1



MiniSKiiP[®] 3

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKIIP 38NAB066V1

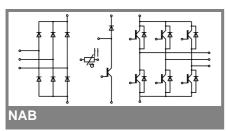
Target Data

Features

- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

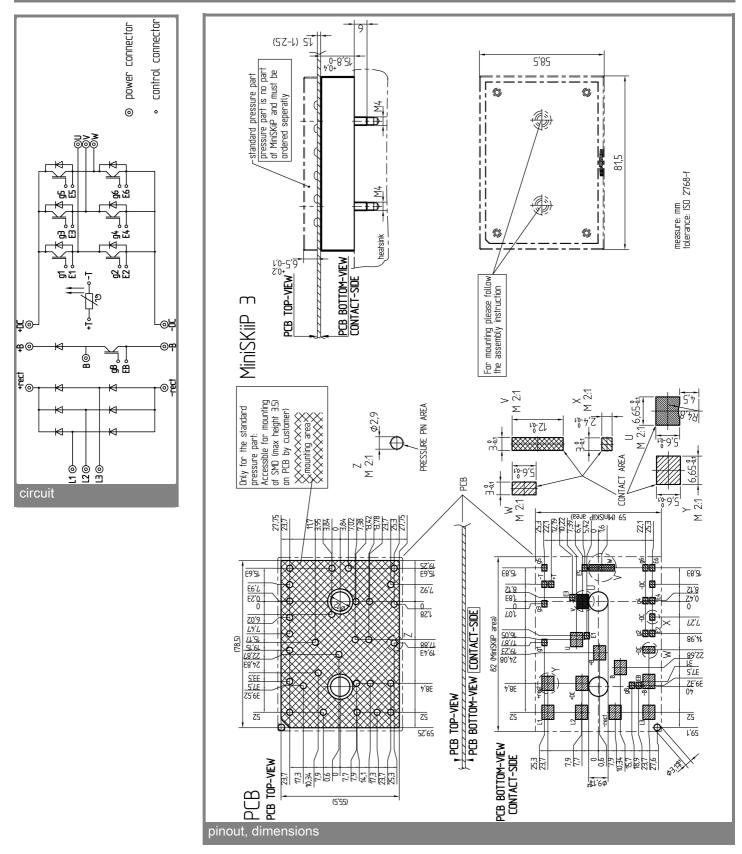
- Inverter up to 22 kVA
- Typical motor power 11 kW



Absolute	Maximum Ratings	$T_s = 25 \ ^{\circ}C$, unless otherwise	specified					
Symbol	Conditions	Values	Units					
IGBT - Inverter, Chopper								
V _{CES}		600	V					
I _C	T _s = 25 (70) °C		A					
ICRM	$T_s = 25 (70) \ ^{\circ}C, t_p \le 1 \ ms$		A					
V _{GES}		± 15	V					
Т _ј		- 40 + 150	°C					
Diode - Inverter, Chopper								
I _F	T _s = 25 (70) °C		А					
I _{FRM}	$T_s = 25 (70) \ ^{\circ}C, t_p \le 1 \ ms$		А					
Т _ј		- 40 + 150	°C					
Diode - Rectifier								
V _{RRM}		800	V					
I _F	T _s = 70 °C	61	А					
I _{FSM}	t _p = 10 ms, sin 180 °, T _j = 25 °C	700	А					
i²t	t _p = 10 ms, sin 180 °, T _j = 25 °C	2400	A²s					
Т _ј		- 40 + 150	°C					
I _{tRMS}	per power terminal (20 A / spring)	80	А					
T _{stg}	$T_{op} \leq T_{stg}$	- 40 + 125	°C					
V _{isol}	AC, 1 min.	2500	V					

Characteristics		T_s = 25 °C, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
IGBT - Inv	verter, Chopper					
V _{CEsat}	I _C = 100 A, T _i = 25 (125) °C		2 (2,2)	2,5 (2,7)	V	
V _{GE(th)}	$V_{GE} = V_{CE}$, $I_C = 2 \text{ mA}$	3	4	5	V	
V _{CE(TO)}	T _i = 25 (125) °C		1,2 (1,1)	1,3 (1,2)	V	
r _T	T _i = 25 (125) °C		8 (11)	12 (15)	mΩ	
Cies	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		5,4		nF	
C _{oes}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1,1		nF	
C _{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1,3		nF	
R _{th(j-s)}	per IGBT		0,5		K/W	
t _{d(on)}	under following conditions		42		ns	
t, Č	V _{CC} = 300 V, V _{GE} = ± 15 V		46		ns	
t _{d(off)}	I _C = 100 A, T _i = 125 °C		333		ns	
t _f	$R_{Gon} = R_{Goff} = 12 \Omega$		40		ns	
E _{on}	inductive load		2,1		mJ	
E _{off}			2,6		mJ	
Diode - Ir	verter, Chopper					
V _F = V _{EC}	I _F = 100 A, T _i = 25 (125) °C		1,6 (1,6)	1,9 (1,9)	V	
V _(TO)	T _i = 25 (125) °C		1 (0,9)	1,1 (1)	V	
r _T	T _i = 25 (125) °C		6 (7)	8 (9)	mΩ	
R _{th(j-s)}	per diode		0,7		K/W	
I _{RRM}	under following conditions		92		Α	
Q _{rr}	I _F = 100 A, V _B = 300 V		9,1		μC	
Err	V _{GE} = 0 V, T _i = 125 °C		1,8		mJ	
	di _F /dt = 2350 A/µs					
Diode - R	ectifier					
V _F	I _F = 35 A, T _i = 25 °C		1,1		V	
V _(TO)	$T_{i} = 150 \ ^{\circ}C$		0,8		V	
r _T	T _i = 150 °C		11		mΩ	
R _{th(j-s)}	per diode		0,9		K/W	
	ture Sensor	1			1	
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω	
Mechanic		1	. ,			
w			95		g	
Ms	Mounting torque	2		2,5	Nm	

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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